

Jianping Liu

List of Publications by Year in descending order

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38
papers

766
citations

687363

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h-index

526287

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38
times ranked

1004
citing authors

#	ARTICLE	IF	CITATIONS
1	Greatly suppressed potential inhomogeneity and performance improvement of c-plane InGaN green laser diodes. <i>Science China Materials</i> , 2022, 65, 543-546.	6.3	8
2	Growth Behaviors of GaN on Stripes of Patterned c-Plane GaN Substrate. <i>Nanomaterials</i> , 2022, 12, 478.	4.1	3
3	Carrier recombination dynamics in green InGaN-LEDs with quantum-dot-like structures. <i>Journal of Materials Science</i> , 2021, 56, 1481-1491.	3.7	3
4	The Significant Effect of Carbon and Oxygen Contaminants at Pd/p-GaN Interface on Its Ohmic Contact Characteristics. <i>Physica Status Solidi (A) Applications and Materials Science</i> , 2021, 218, 2000603.	1.8	2
5	High power GaN-based blue superluminescent diodes with low spectral modulation. <i>AIP Advances</i> , 2021, 11, .	1.3	1
6	Effect of Graded-Indium-Content Superlattice on the Optical and Structural Properties of Yellow-Emitting InGaN/GaN Quantum Wells. <i>Materials</i> , 2021, 14, 1877.	2.9	5
7	Multiwavelength GaN-Based Surface-Emitting Lasers and Their Design Principles. <i>Annalen Der Physik</i> , 2020, 532, 1900308.	2.4	5
8	Design and growth of GaN-based blue and green laser diodes. <i>Science China Materials</i> , 2020, 63, 1348-1363.	6.3	32
9	On-Chip Hyperuniform Lasers for Controllable Transitions in Disordered Systems. <i>Laser and Photonics Reviews</i> , 2020, 14, 1800296.	8.7	10
10	Effects of Lateral Optical Confinement In GaN VCSELs With Double Dielectric DBRs. <i>IEEE Photonics Journal</i> , 2020, 12, 1-8.	2.0	8
11	Suppression of substrate mode in GaN-based green laser diodes. <i>Optics Express</i> , 2020, 28, 15497.	3.4	9
12	High-power hybrid GaN-based green laser diodes with ITO cladding layer. <i>Photonics Research</i> , 2020, 8, 279.	7.0	33
13	Strain-Related Degradation of GaN-Based Blue Laser Diodes. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2019, 25, 1-5.	2.9	0
14	GaN in different dimensionalities: Properties, synthesis, and applications. <i>Materials Science and Engineering Reports</i> , 2019, 138, 60-84.	31.8	39
15	Polarization relaxation in InGaN/(In)GaN multiple quantum wells. <i>Japanese Journal of Applied Physics</i> , 2019, 58, SCCB12.	1.5	1
16	Room temperature continuous wave lasing of GaN-based green vertical-cavity surface-emitting lasers. , 2019, , .		1
17	Room-Temperature Electrically Injected AlGaN-Based near-Ultraviolet Laser Grown on Si. <i>ACS Photonics</i> , 2018, 5, 699-704.	6.6	37
18	Green Vertical-Cavity Surface-Emitting Lasers Based on Combination of Blue-Emitting Quantum Wells and Cavity-Enhanced Recombination. <i>IEEE Transactions on Electron Devices</i> , 2018, 65, 4401-4406.	3.0	8

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19	Room-temperature continuous-wave electrically pumped InGaN/GaN quantum well blue laser diode directly grown on Si. <i>Light: Science and Applications</i> , 2018, 7, 13.	16.6	101
20	Significant increase of quantum efficiency of green InGaN quantum well by realizing step-flow growth. <i>Applied Physics Letters</i> , 2017, 111, 112102.	3.3	15
21	Asymmetrical quantum well degradation of InGaN/GaN blue laser diodes characterized by photoluminescence. <i>Applied Physics Letters</i> , 2017, 111, 212102.	3.3	7
22	Green laser diodes with low threshold current density via interface engineering of InGaN/GaN quantum well active region. <i>Optics Express</i> , 2017, 25, 415.	3.4	34
23	GaN-Based Blue Laser Diodes With 2.2 W of Light Output Power Under Continuous-Wave Operation. <i>IEEE Photonics Technology Letters</i> , 2017, 29, 2203-2206.	2.5	22
24	Green laser diodes with low operation voltage obtained by suppressing carbon impurity in AlGaIn: Mg cladding layer. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2016, 13, 245-247.	0.8	9
25	Influence of residual carbon impurities in i-GaN layer on the performance of GaN-based p-i-n photodetectors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016, 34, 011204.	1.2	4
26	Investigation of breakdown mechanism during field emission process of AlN thin film microscopic cold cathode. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016, 34, 012201.	1.2	1
27	Investigation of InGaN/GaN laser degradation based on luminescence properties. <i>Journal of Applied Physics</i> , 2016, 119, .	2.5	14
28	Room-temperature continuous-wave electrically injected InGaIn-based laser directly grown on Si. <i>Nature Photonics</i> , 2016, 10, 595-599.	31.4	191
29	Catastrophic Degradation of InGaIn/GaN Blue Laser Diodes. <i>IEEE Transactions on Device and Materials Reliability</i> , 2016, 16, 638-641.	2.0	3
30	Utilization of polarization-inverted AlInGaIn or relatively thinner AlGaIn electron blocking layer in InGaIn-based blue-violet laser diodes. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2015, 33, 011209.	1.2	8
31	Detection of a Superconducting Phase in a Two-Atom Layer of Hexagonal Ga Film Grown on Semiconducting GaN(0001). <i>Physical Review Letters</i> , 2015, 114, 107003.	7.8	81
32	Injection current dependences of electroluminescence transition energy in InGaIn/GaN multiple quantum wells light emitting diodes under pulsed current conditions. <i>Journal of Applied Physics</i> , 2015, 118, 033101.	2.5	17
33	Enhanced temperature characteristic of InGaIn/GaN laser diodes with uniform multiple quantum wells. <i>Semiconductor Science and Technology</i> , 2015, 30, 125015.	2.0	6
34	Performance comparison of front- and back-illuminated modes of the AlGaIn-based p-i-n solar-blind ultraviolet photodetectors. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2014, 32, 031204.	1.2	9
35	Direct periodic patterning of GaN-based light-emitting diodes by three-beam interference laser ablation. <i>Applied Physics Letters</i> , 2014, 104, 141105.	3.3	9
36	Characteristics of InGaIn-based superluminescent diodes with one-sided oblique cavity facet. <i>Science Bulletin</i> , 2014, 59, 1903-1906.	1.7	4

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37	Hillock formation and suppression on c-plane homoepitaxial GaN Layers grown by metalorganic vapor phase epitaxy. Journal of Crystal Growth, 2013, 371, 7-10.	1.5	23
38	Optimization of the cavity facet coating in high power GaN-based semiconductor laser diodes. Science China Technological Sciences, 2012, 55, 883-887.	4.0	3